

# InGaN Venus Blue LED Chip

Type:

**ES-CABL V38**

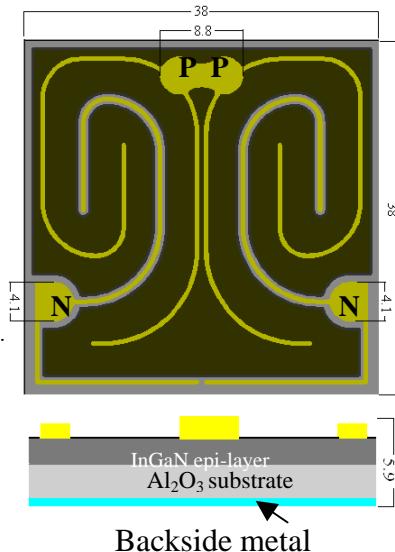
Unit: mil

## Features:

- (1) High luminous intensity
- (2) Long operation life
- (3) 100% probing test
- (4) Passivation layer on top
- (5) Backside mirror layer

## Characteristics:

- (1) Size  
Chip size : 38 mil x 38 mil ( $965\pm25\mu\text{m}$  x  $965\pm25\mu\text{m}$ )  
Chip thickness : 5.9 mil ( $150\pm10\mu\text{m}$ )  
P bonding pad x 2 : 3.9 mil ( $100\pm10\mu\text{m}$ )  
N bonding pad x 2 : 4.1 mil ( $105\pm10\mu\text{m}$ )
- (2) Metallization  
P electrode : Au alloy  
N electrode : Au alloy  
Backside metal : Au alloy
- (3) Structure  
Refer to drawing



## Electro-optical characteristics:<sup>(1)</sup>

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage	V <sub>f1</sub>	I <sub>f</sub> = 10uA	1.6	---	---	V
	V <sub>f2</sub>	I <sub>f</sub> = 350mA	---	3.5	3.8	V
Reverse current	I <sub>r</sub>	V <sub>r</sub> = 5V	---	---	2	uA
Dominant wavelength <sup>(2)</sup>	λ <sub>d</sub>	I <sub>f</sub> = 350mA	455	460	465	nm
Radiant power <sup>(3)(4)</sup>	P <sub>o</sub>	H13 H14	I <sub>f</sub> = 350mA	185	---	220
				220	---	255

- (1) ESD protection during chip handling is recommended.
- (2) Basically, wavelength uniformity is  $\lambda_d \pm 5\text{nm}$ ; however, customers' special requirements are also welcome.
- (3) Customer's special requirements are also welcome.
- (4) Radiant power is determined by a correlation with luminous intensity using a Au-plated TO-18 header without an encapsulant, whereas luminous intensity is measured by EPISTAR's equipment on bare chips.
- (5) Epistar maintains a tolerance of  $\pm 15\%$  on the above radiant flux specifications.

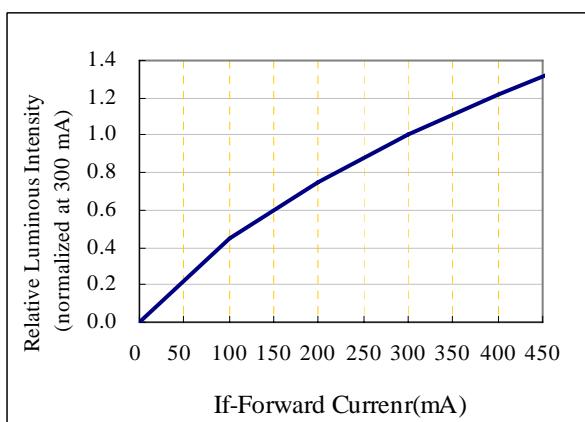


Fig-1 Relative Luminous Intensity vs. Forward current

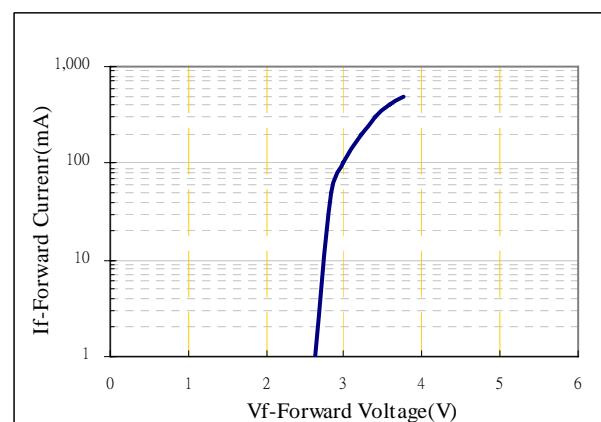


Fig-2 Forward Current vs. Forward Voltage

## Absolute maximum ratings:

Parameter	Symbol	Condition	Rating	Unit
Forward DC current	I <sub>f</sub>	T <sub>a</sub> =25°C	≤ 450	mA
Reverse voltage	V <sub>r</sub>	T <sub>a</sub> =25°C	≤ 5	V
Junction temperature	T <sub>j</sub>	---	≤ 115	°C
Storage temperature	T <sub>stg</sub>	chip	-40 ~ +85	°C
		chip-on-tape/storage	0 ~ 40	°C
		chip-on-tape/transportation	-20 ~ +65	°C
Temperature during packaging	---	---	280(<10sec)	°C

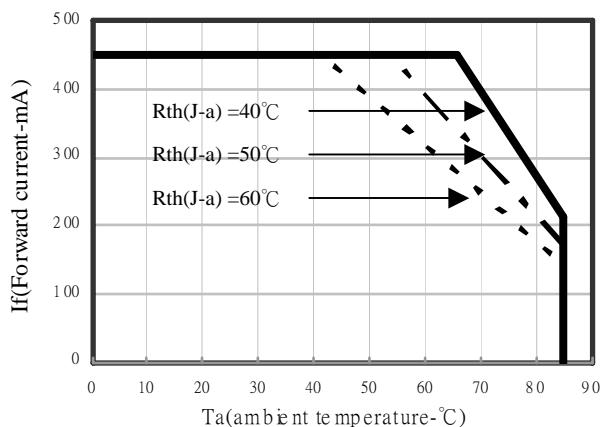


Fig-3 Maximum Driving Forward DC Current vs. mbient Temperature (Derating based on T<sub>j</sub> max. = 115°C)

## Applications:

- Backlighting for display and projector
- Signage and channel letters
- Decorating and entertainment lighting
- Architectural and specialty lighting
- Indoor/outdoor application
- Portable light source